

Silicon PNP Power Transistors

2SB566 2SB566A

DESCRIPTION

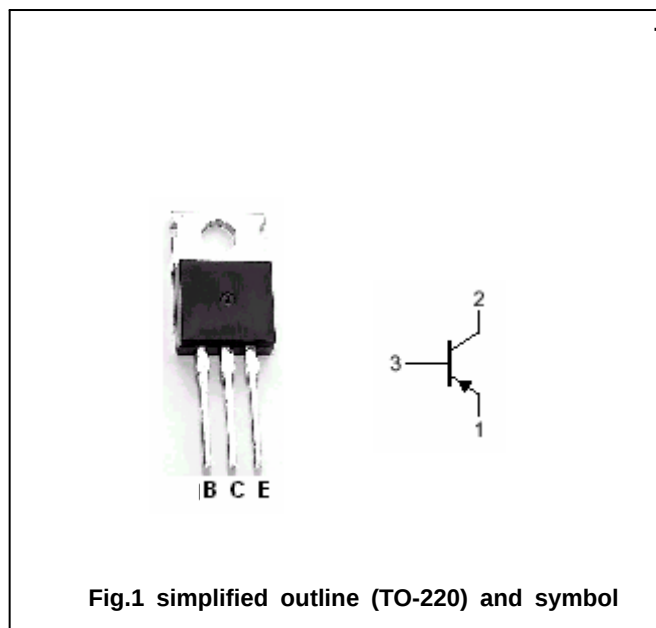
- With TO-220C package
- Complement to type 2SD476/476A

APPLICATIONS

- For low frequency power amplifier power switching applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

Absolute maximum ratings($T_c=25^\circ\text{C}$)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage		Open emitter	-70	V
V_{CEO}	Collector-emitter voltage	2SB566	Open base	-50	V
		2SB566A		-60	
V_{EBO}	Emitter-base voltage		Open collector	-5	V
I_C	Collector current			-4	A
I_{CM}	Collector current-peak			-8	A
P_C	Collector power dissipation		$T_c=25$	40	W
T_j	Junction temperature			150	
T_{stg}	Storage temperature			-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CBO}	Collector-base breakdown voltage		I _C =-10 μA ; I _E =0	-70			V
V _{(BR)CEO}	Collector-emitter breakdown voltage	2SB566	I _C =-50mA; R _{BE} =∞	-50			V
		2SB566A		-60			
V _{(BR)EBO}	Emitter-base breakdown voltage		I _E =-10 μA; I _C =0	-5			V
V _{CEsat}	Collector-emitter saturation voltage		I _C =-2 A; I _B =-0.2 A			-1.0	V
V _{BEsat}	Base-emitter saturation voltage		I _C =-2 A; I _B =-0.2 A			-1.2	V
I _{CBO}	Collector cut-off current		V _{CB} =-50V; I _E =0			-1	μA
h _{FE-1}	DC current gain		I _C =-0.1A ; V _{CE} =-4V	35			
h _{FE-2}	DC current gain		I _C =-1A ; V _{CE} =-4V	60		200	
f _T	Transition frequency		I _C =-0.5A ; V _{CE} =-4V		15		MHz

Switching times

t _{on}	Turn-on time	I _C =-0.5A ; V _{CC} =-10.5V I _{B1} =-I _{B2} =-0.05 A		0.3		μs
t _{off}	Turn-off time			3.0		μs
t _{stg}	Storage time			2.5		μs

◆ h_{FE-2} classifications

B	C
60-120	100-200

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Technical drawing of a mechanical part showing three views: front, side, and top. The dimensions are as follows:

- Front View:**
 - Total width: 10.00
 - Distance from left edge to center hole: 8.76
 - Top flange thickness: 2.80
 - Distance from top flange to center hole: 0.00
 - Distance from center hole to right edge: 0.45
 - Distance from center hole to bottom flange: 3.75
 - Distance from bottom flange to top of slots: 8.30
 - Distance from top of slots to bottom of slots: 13.00
 - Distance from bottom of slots to base: 15.80
 - Distance from left edge to first slot: 30.00°
 - Distance from first slot to second slot: 1.20
 - Distance from second slot to third slot: 0.80
 - Distance from third slot to right edge: 15.00°
 - Distance from left edge to center of first slot: 5.08
- Side View:**
 - Total height: 1.300 ± 0.01
 - Distance from top to first step: 6.55
 - Distance from first step to second step: 5.00°
 - Distance from second step to third step: 9.25
 - Distance from third step to base: 5.00°
 - Distance from base to right edge: 0.45 ± 0.01
 - Distance from left edge to right edge: 2.60
- Top View:**
 - Width: 4.30
 - Depth: 15.00

Fig.2 Outline dimensions (unindicated tolerance: ± 0.10 mm)

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